CMP107N20/CMB107N20/CMI107N20/CMF107N20

200V, 8.5mΩ typ., 105A N-Channel MOSFET

General Description

The 107N20 uses advanced SGT technology to provide excellent RDS(ON).This device is ideal for high-frequency switching and synchronous rectification.

Product Summary

BVDSS	$R_{DS(on)}$ max.	ID
200V	10mΩ	105A

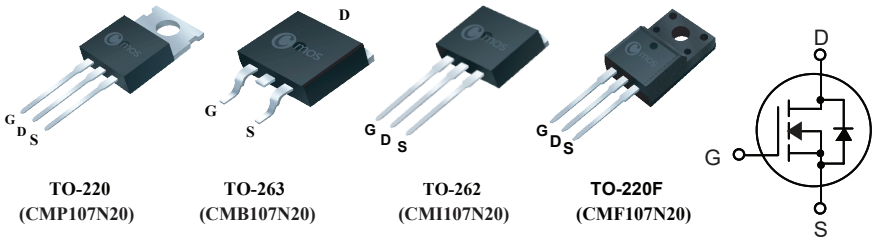
Applications

- Motor control and drive
- Battery management
- Uninterruptible Power Supply

Features

- Low On-Resistance
- 100% avalanche tested
- Low Gate Charge
- RoHS Compliant

TO-220/263/262/220F Pin Configuration



TO-220 (CMP107N20) | TO-263 (CMB107N20) | TO-262 (CMI107N20) | TO-220F (CMF107N20)

Absolute Maximum Ratings

Symbol	Parameter	220/263/262	220F	Units
V_{DS}	Drain-Source Voltage	200		V
V_{GS}	Gate-Source Voltage	±20		V
I_D@T_C=25℃	Continuous Drain Current	105	105*	A
I_D@T_C=100℃	Continuous Drain Current	67	67*	A
I_{DM}	Pulsed Drain Current	420	420*	A
EAS	Single Pulse Avalanche Energy (Note 1)	2311		mJ
P_D@T_C=25℃	Total Power Dissipation	300	65	W
T_{STG}	Storage Temperature Range	-55 to 150		℃
T_J	Operating Junction Temperature Range	150		℃

* Drain current limited by maximum junction temperature.

Thermal Data

Symbol	Parameter	220/263/262	220F	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient Max.(min. footprint)	62.5	62.5	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-case Max.	0.42	1.92	℃/W

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Electrical Characteristics (T_J=25℃ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	200	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=50A (TO-220)	---	8.5	10	mΩ
		V_{GS}=10V , I_D=50A (TO-263)	---	8.3	9.5	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250μA	2	---	4	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=200V , V_{GS}=0V	---	---	1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=10V, I_D =20A	---	46	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	3.2	---	Ω
Q_g	Total Gate Charge	V_{DS}=100V , I_D=50A V_{GS}=10V	---	69	---	nC
Q_{gs}	Gate-Source Charge		---	25	---	
Q_{gd}	Gate-Drain Charge		---	16	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DS}=100V , V_{GS}=10V , I_D=50A R_G =2.7Ω	---	16	---	ns
T_r	Rise Time		---	82	---	
$T_{d(off)}$	Turn-Off Delay Time		---	55	---	
T_f	Fall Time		---	84	---	
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , f=1MHz	---	5450	---	pF
C_{oss}	Output Capacitance		---	3150	---	
C_{rss}	Reverse Transfer Capacitance		---	140	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	105	A
I_{SM}	Pulsed Source Current		---	---	420	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=50A ,T_J=25℃	---	0.83	1.4	V
t_{rr}	Reverse Recovery Time	di/dt = 100A/μs T_J =25℃ , I_{SD} =50A	---	129	---	ns
Q_{rr}	Reverse Recovery Charge		---	752	---	nC

Note :

1.The EAS data shows Max. rating .The test condition is V_{DS}=80V , V_{GS}=10V , L=10mH , I_{AS}=21.5A.

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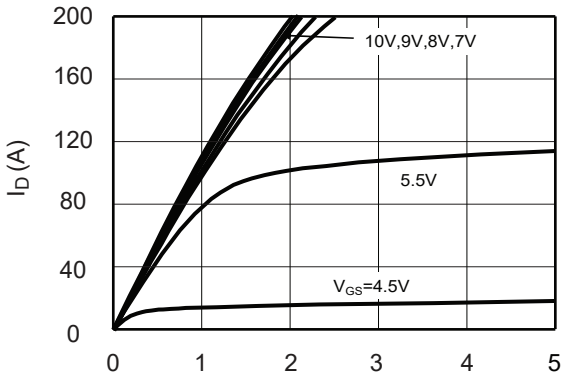
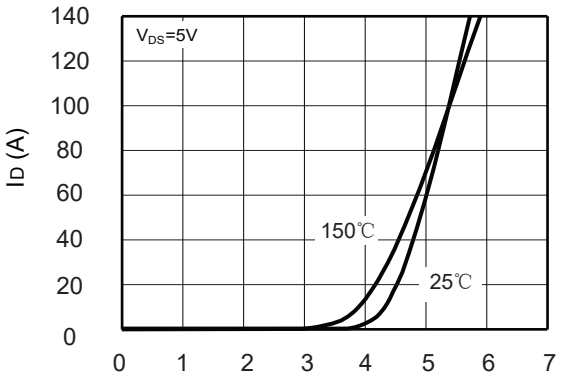
Cmos reserver the right to improve product design ,functions and reliability wihtout notice.Please refer to the latest version of specification.

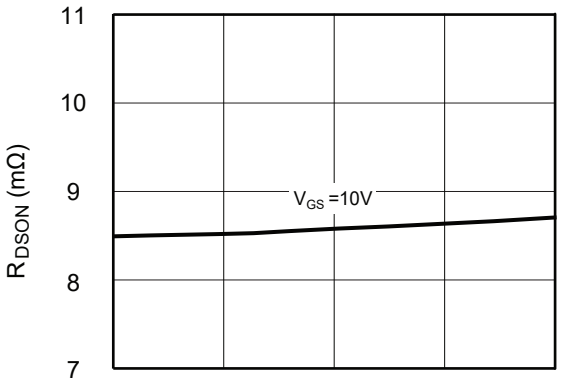
Typical Characteristics



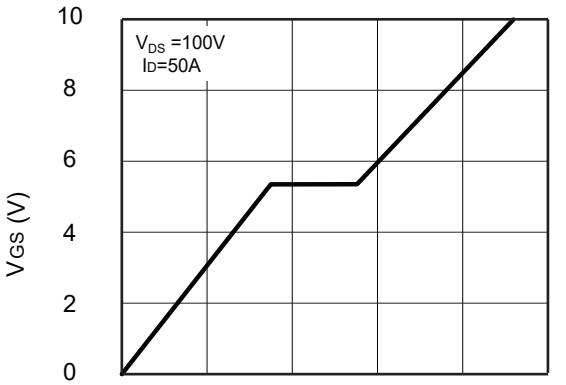
Output Characteristics



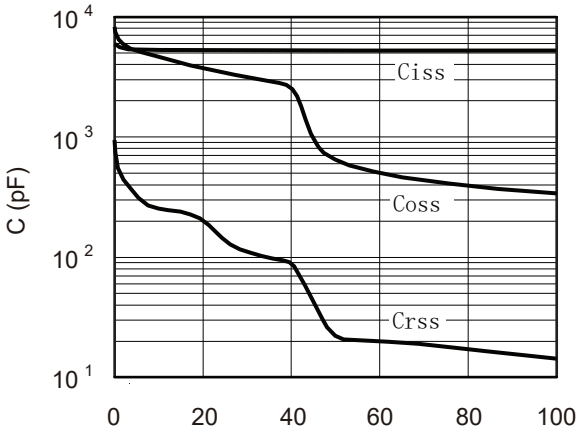
transfer characteristics



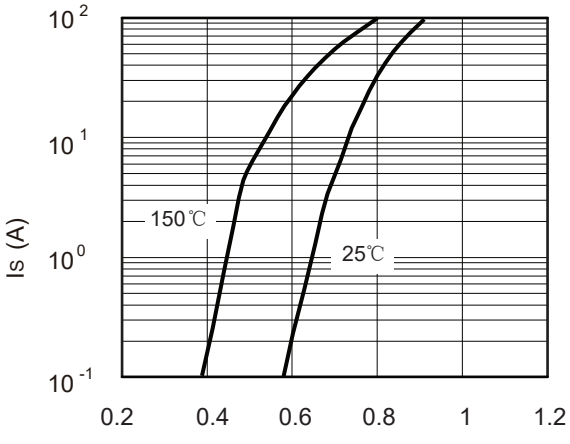
drain-source on-resistance



Gate charge vs gate-source voltage

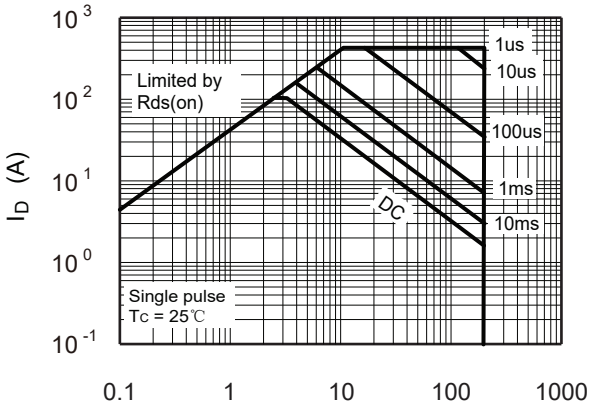


Capacitance Characteristics

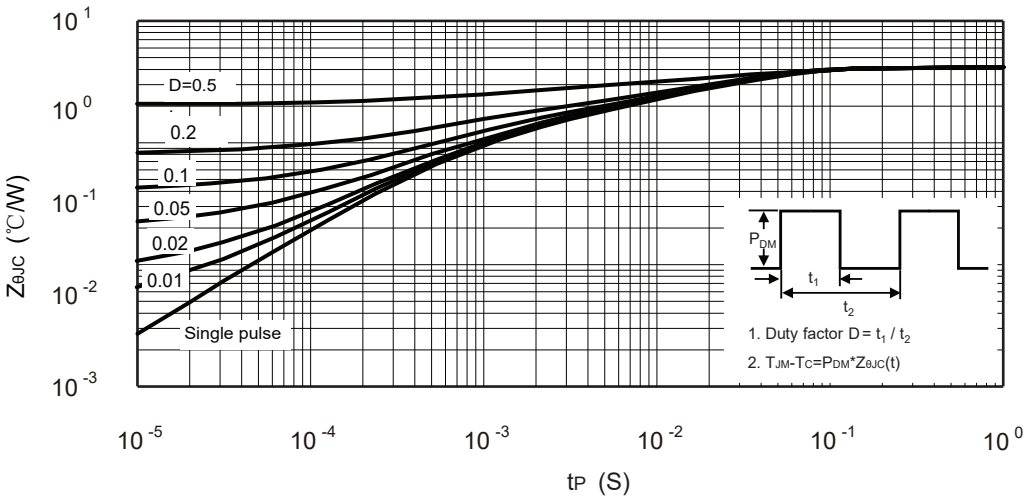


Body-Diode Characteristics

Typical Characteristics



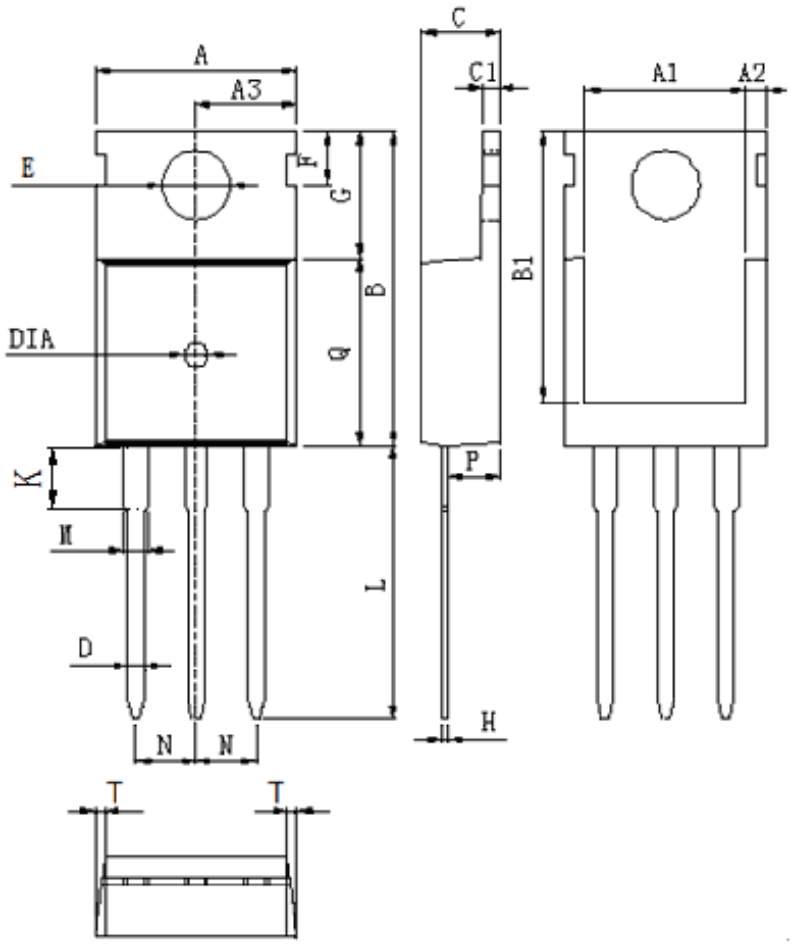
Safe Operating Area



Transient thermal impedance(220,262,263)

Package Dimension

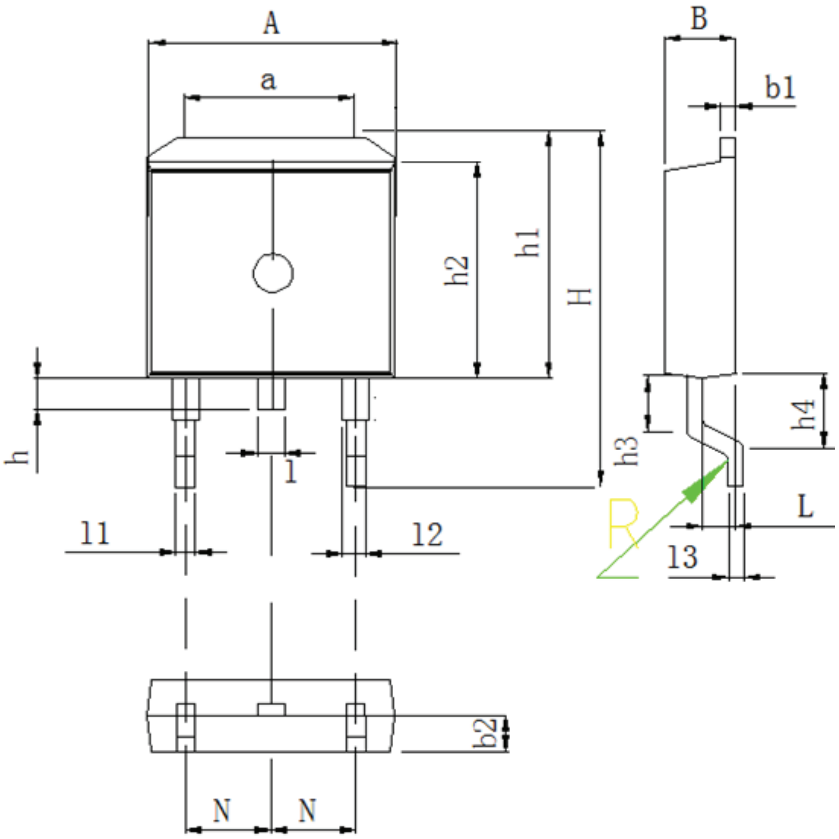
TO-220 Unit :mm



DIM	MILLIMETERS
A	10.0±0.3
A1	8.64±0.2
A2	1.15±0.1
A3	5.0±0.2
B	15.8±0.4
B1	13.2±0.3
C	4.56±0.1
C1	1.3±0.2
D	0.8±0.2
E	3.6±0.2
F	2.95±0.3
G	6.5±0.3
H	0.5±0.1
K	3.1±0.2
L	13.2±0.4
M	1.25±0.1
N	2.54±0.1
P	2.4±0.3
Q	9.0±0.3
T	W:0.35
DIA	⊙1.5(deep 0.2)

Package Dimension

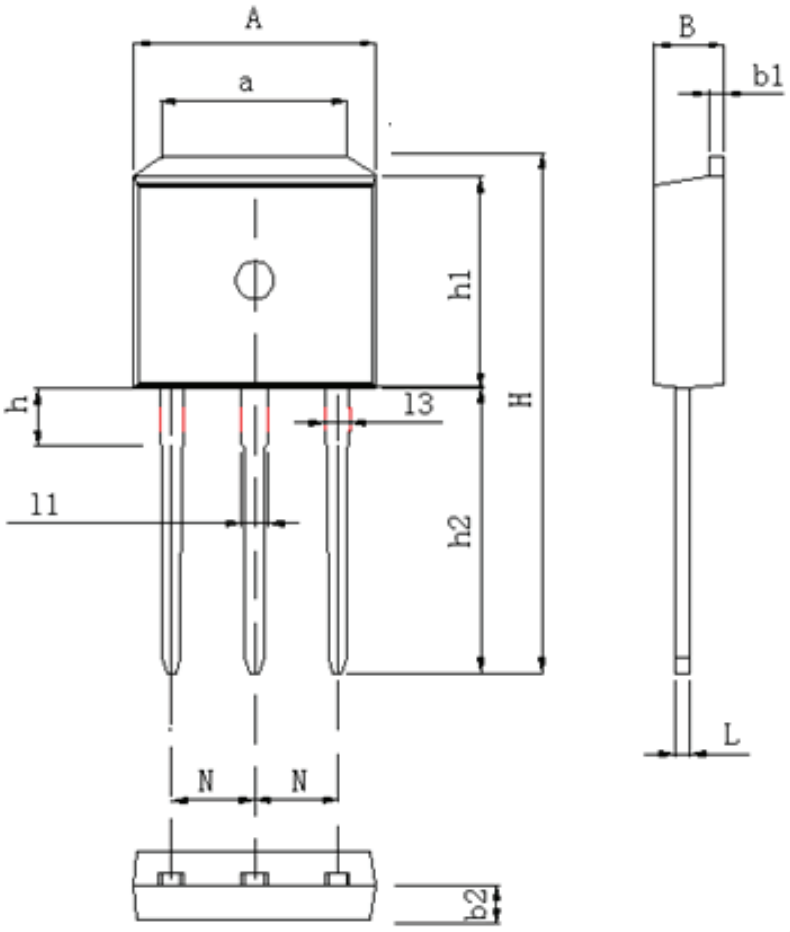
TO-263 Unit :mm



DIM	MILLIMETERS
A	9.8±0.2
a	7.4±0.4
B	4.5±0.2
b1	1.3±0.05
b2	2.4±0.2
H	15.5±0.3
h	1.54±0.2
h1	10.5±0.2
h2	9.2±0.1
h3	1.54±0.2
h4	2.7±0.2
L	2.4±0.2
l	1.3±0.1
l1	0.8±0.1
l2	1.3±0.1
l3	0.5±0.1
N	2.54±0.1
R	0.5R±0.05

Package Dimension

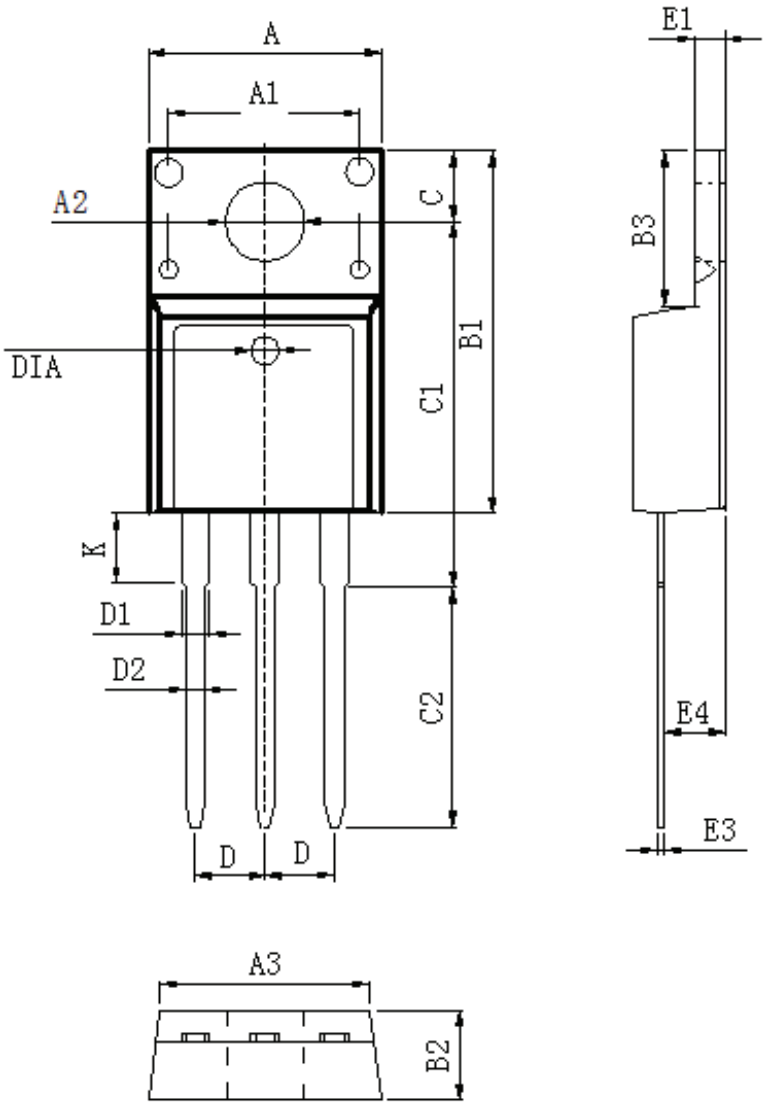
TO-262 Unit :mm



DIM	MILLIMETERS
A	9.98±0.2
a	7.4±0.4
B	4.5±0.2
b1	1.3±0.05
b2	2.4±0.2
H	23.9±0.3
h	3.1±0.2
h1	9.16±0.2
h2	13.2±0.2
L	0.5±0.1
l1	1.3±0.1
l2	0.8±0.1
N	2.45±0.1

Package Dimension

TO-220F Unit :mm



DIM	MILLIMETERS
A	10.16±0.3
A1	7.00±0.1
A2	3.3±0.2
A3	9.5±0.2
B1	15.87±0.3
B2	4.7±0.2
B3	6.68±0.4
C	3.3±0.2
C1	12.57±0.3
C2	10.02±0.5
D	2.54±0.05
D1	1.28±0.2
D2	0.8±0.1
K	3.1±0.3
E1	2.54±0.1
E3	0.5±0.1
E4	2.76±0.2
DIA	⊙1.5(deep 0.2)